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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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1SS119

Silicon Epitaxial Planar Diode for High Speed Switching

RENESAS

ADE-208-180B (Z)

Rev.2
Sep. 2000

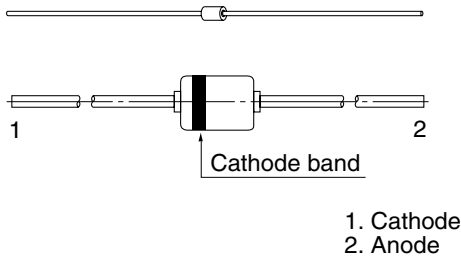
Features

- Low capacitance. ($C = 3.0 \text{ pF max}$)
- Short reverse recovery time. ($t_r = 3.5 \text{ ns max}$)
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Package Code
1SS119	Light Blue	MHD

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	35	V
Reverse voltage	V_R	30	V
Average rectified current	I_O	150	mA
Peak forward current	I_{FM}	450	mA
Non-Repetitive peak forward surge current	I_{FSM}^*	1	A
Power dissipation	Pd	250	mW
Junction temperature	Tj	175	°C
Storage temperature	Tstg	-65 to +175	°C

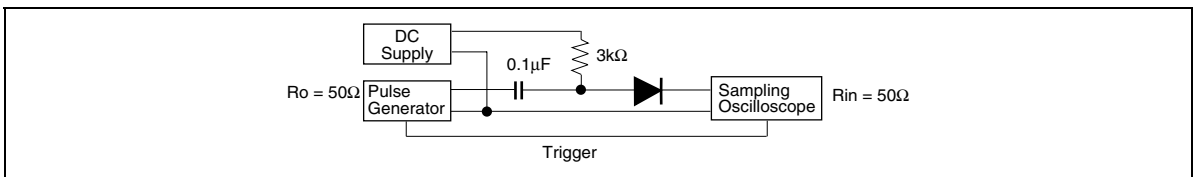
Note: Within 1s forward surge current.

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.8	V	$I_F = 10 \text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 30 \text{ V}$
Capacitance	C	—	—	3.0	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
Reverse recovery time	t_{rr}^*	—	—	3.5	ns	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 50 \Omega$

Note: Reverse recovery time test circuit



Main Characteristic

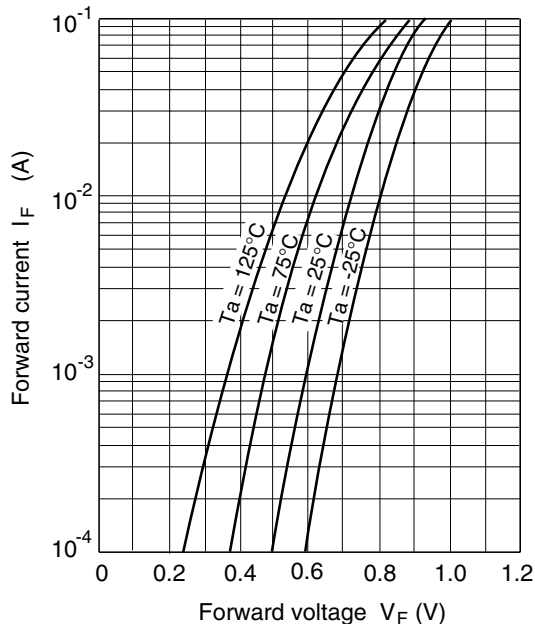


Fig.1 Forward current Vs. Forward voltage

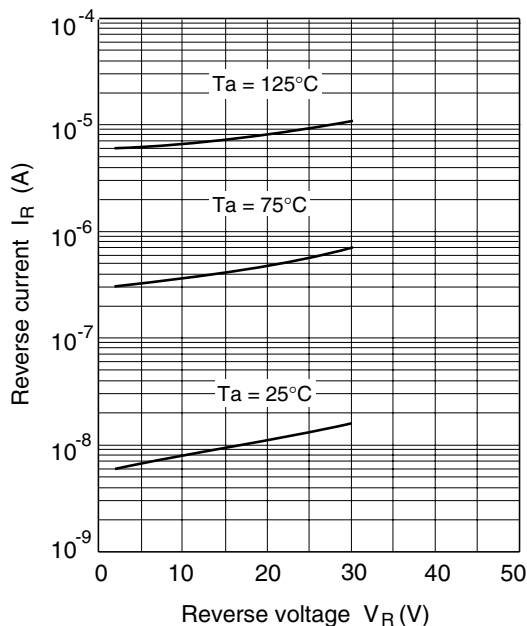


Fig.2 Reverse current Vs. Reverse voltage

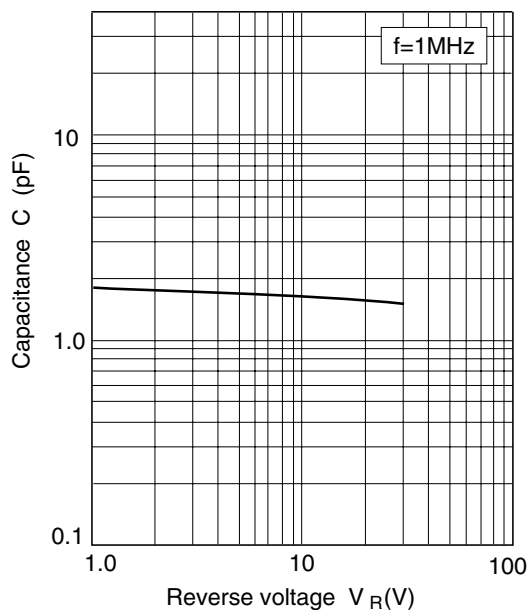
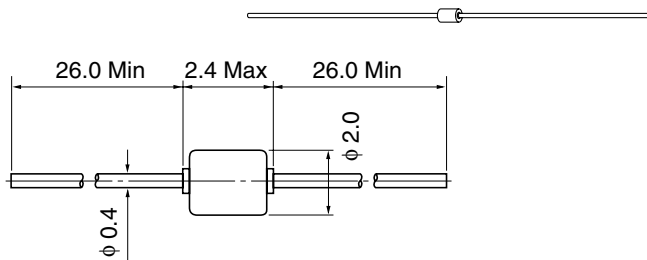


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



Hitachi Code	MHD
JEDEC	Conforms
EIAJ	—
Mass (reference value)	0.084 g

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Sales Offices

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe Ltd. Electronic Components Group Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 585200	Hitachi Asia Ltd. Hitachi Tower 16 Collyer Quay #20-00 Singapore 049318 Tel: <65>-538-6533/538-8577 Fax: <65>-538-6933/538-3877 URL: http://www.hitachi.com.sg	Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon Hong Kong Tel: <852>-(2)-735-9218 Fax: <852>-(2)-730-0281 URL: http://semiconductor.hitachi.com.hk
	Hitachi Europe GmbH Electronic Components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00	Hitachi Asia Ltd. (Taipei Branch Office) 4/F, No. 167, Tun Hwa North Road Hung-Kuo Building Taipei (105), Taiwan Tel: <886>-(2)-2718-3666 Fax: <886>-(2)-2718-8180 Telex: 23222 HAS-TP URL: http://www.hitachi.com.tw	

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